



Welcome to E-XFL.COM

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Obsolete
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	CANbus, I ² C, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	72
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str731fv1t6

6	Order codes	49
7	Known limitations	50
	7.1 Low power wait for interrupt mode	50
	7.2 PLL free running mode at high temperature	50
8	Revision history	51

1 Scope

This datasheet provides the STR73x ordering information, mechanical and electrical device characteristics.

For complete information on the STR73xF microcontroller memory, registers and peripherals, please refer to the STR73x reference manual.

For information on programming, erasing and protection of the internal Flash memory please refer to the STR7 Flash programming reference manual.

For information on the ARM7TDMI core please refer to the ARM7TDMI technical reference manual.

1.1 Description

ARM core with embedded Flash & RAM

STR73xF family combines the high performance ARM7TDMI™ CPU with an extensive range of peripheral functions and enhanced I/O capabilities. All devices have on-chip high-speed single voltage Flash memory and high-speed RAM. The STR73xF family has an embedded ARM core and is therefore compatible with all ARM tools and software.

Extensive tools support

STMicroelectronics' 32-bit, ARM core-based microcontrollers are supported by a complete range of high-end and low-cost development tools to meet the needs of application developers. This extensive line of hardware/software tools includes starter kits and complete development packages all tailored for ST's ARM core-based MCUs.

The range of development packages includes third-party solutions that come complete with a graphical development environment and an in-circuit emulator/programmer featuring a JTAG application interface. These support a range of embedded operating systems (OS), while several royalty-free OSs are also available.

For more information, please refer to ST MCU site <http://www.st.com/mcu>

Figure 1 shows the general block diagram of the device family.



2 Overview

Table 2. Product overview

Features	STR730FZx		STR735FZx		STR731FVx			STR736FVx		
Flash memory - bytes	128K	256K	128K	256K	64K	128K	256K	64K	128K	256K
RAM - bytes	16 K				16 K					
Peripheral functions	10 TIM timers, 112 I/Os, 32 wake-up lines, 16 ADC				6 TIM timers, 72 I/Os, 18 wake-up lines, 12 ADC channels					
CAN peripherals	3		0		3			0		
Operating voltage	4.5 to 5.5 V									
Operating temperature	-40 to +85°C/-40 to +105° C									
Packages	T=TQFP144 20 x 20 H=LFBGA144 10 x10				T=TQFP100 14x14					

Package choice: reduced pin-count TQFP100 or feature-rich 144-pin TQFP or LFBGA

The STR73xF family is available in 3 packages. The TQFP144 and LFBGA144 versions have the full set of all features. The 100-pin version has fewer timers, I/Os and ADC channels. Refer to the Device Summary on Page 1 for a comparison of the I/Os available on each package.

The family includes versions with and without CAN.

High speed Flash memory

The Flash program memory is organized in 32-bit wide memory cells which can be used for storing both code and data constants. It is accessed by CPU with zero wait states @ 36 MHz.

The STR7 embedded Flash memory can be programmed using in-circuit programming or in-application programming.

The Flash memory endurance is 10K write/erase cycles and the data retention is 20 years @ 85° C.

IAP (in-application programming): IAP is the ability to re-program the Flash memory of a microcontroller while the user program is running.

ICP (in-circuit programming): ICP is the ability to program the Flash memory of a microcontroller using JTAG protocol while the device is mounted on the user application board.

The Flash memory can be protected against different types of unwanted access (read/write/erase). There are two types of protection:

- Sector write protection
- Flash debug protection (locks JTAG access)

Flexible power management

To minimize power consumption, you can program the STR73xF to switch to SLOW, WFI LPWFI, STOP or HALT modes depending on the current system activity in the application.

clock/calendar/alarm function. When the STR73xF is in LPWFI mode the RTC keeps running, powered by the low power voltage regulator.

UARTs

The 4 UARTs allow full duplex, asynchronous, communications with external devices with independently programmable TX and RX baud rates up to 625 Kbaud.

Buffered serial peripheral interfaces (BSPI)

Each of the three BSPIs allow full duplex, synchronous communications with external devices, master or slave communication at up to 6 Mb/s in master mode and up to 4.5 Mb/s in slave mode (@36 MHz system clock).

I²C interfaces

The two I²C Interfaces provide multi-master and slave functions, support normal and fast I²C mode (400 kHz) and 7 or 10-bit addressing modes.

A/D converter

The 10-bit analog to digital converter, converts up to 16 channels in single-shot or continuous conversion modes (12 channels in 100-pin devices). The minimum conversion time is 3 μ s.

Watchdog

The 16-bit watchdog timer protects the application against hardware or software failures and ensures recovery by generating a reset.

I/O ports

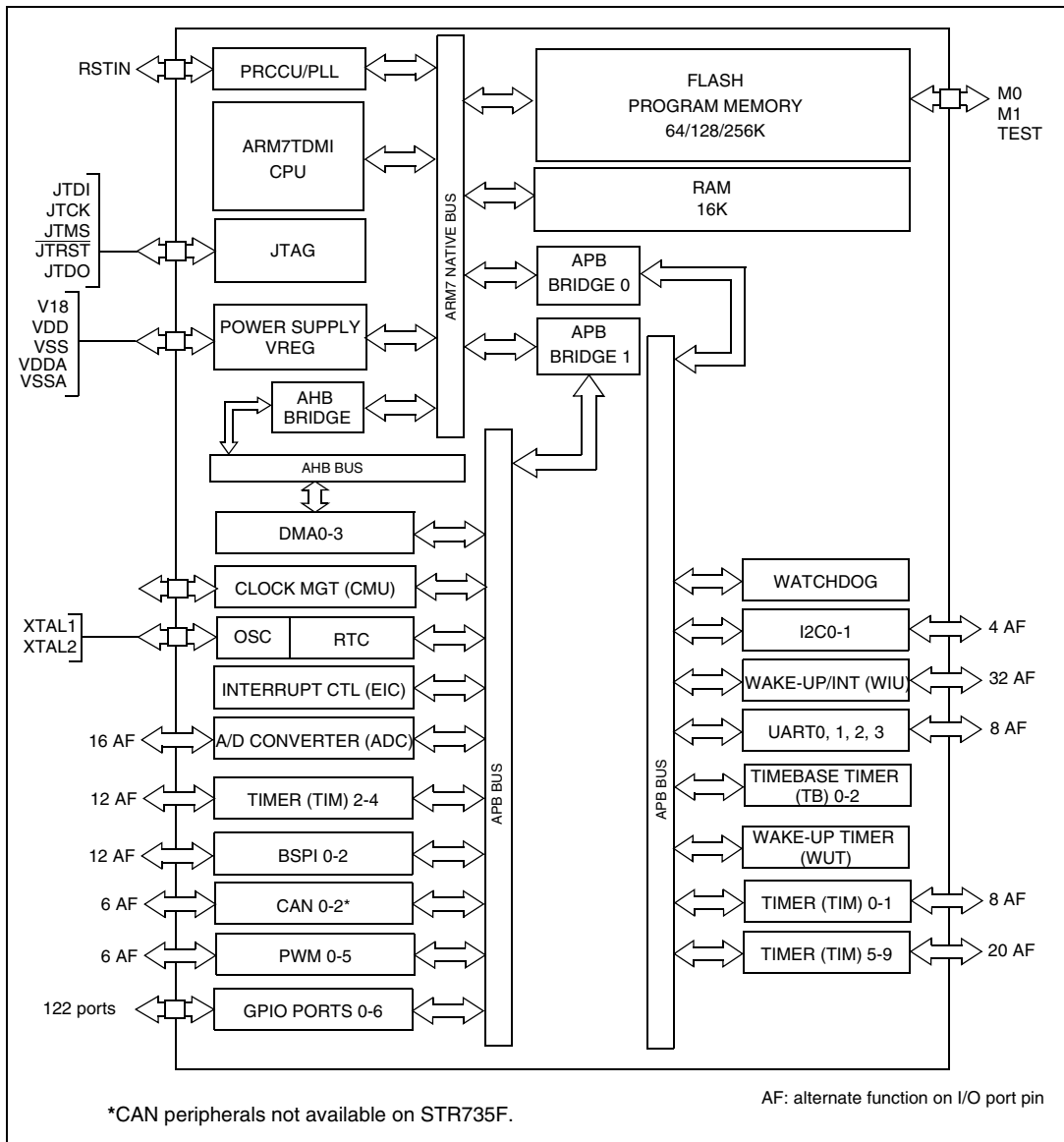
Up to 112 I/O ports (72 in 100-pin devices) are programmable as general purpose input/output or alternate function.

External interrupts and wake-up lines

16 external interrupts lines are available for application use. In addition, up to 32 external Wake-up lines (18 in 100-pin devices) can be used as general purpose interrupts or to wake-up the application from STOP mode.

3 Block diagram

Figure 1. STR730F/STR735F block diagram



Legend / Abbreviations for Table 4:

Type: I = input, O = output, S = supply, HiZ= high impedance,

In/Output level: T_T = TTL 0.8 V / 2 V with input trigger
 C_T = CMOS 0.3V_{DD}/0.7V_{DD} with input trigger

Port and control configuration:

Input: pu/pd = with internal 100 k Ω weak pull-up or pull down

Output: OD = open drain (logic level)
 PP = push-pull

Interrupts:

INTx = external interrupt line

WUPx = wake-up interrupt line

The reset state (during and just after the reset) of the I/O ports is input floating (Input tristate TTL mode). To avoid excess power consumption, unused I/O ports must be tied to ground.

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function
TQFP144	LFPGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP		
1	A1	1	P0.0/OCMPB2	I/O	T_T			2mA	X	X	Port 0.0	TIM2: output compare B output
2	B2	2	P0.1/OCMPA2	I/O	T_T			2mA	X	X	Port 0.1	TIM2: output compare A output
3	C2	3	P0.2/ICAPA2	I/O	T_T			2mA	X	X	Port 0.2	TIM2: input capture A input
4	C3	4	P0.3/ICAPB2	I/O	T_T			2mA	X	X	Port 0.3	TIM2: input capture B input
5	D1		V _{SS}	S							Ground	
6	D2		V _{DD}	S							Supply voltage (5 V)	
7	B1	5	P0.4/OCMPA5	I/O	T_T			2mA	X	X	Port 0.4	TIM5: output compare A output
8	C1	6	P0.5/OCMPB5	I/O	T_T			2mA	X	X	Port 0.5	TIM5: output compare B output
9	D3	7	P0.6/ICAPA5	I/O	T_T			2mA	X	X	Port 0.6	TIM5: input capture A input
10	D4		P0.7/ICAPB5	I/O	T_T			2mA	X	X	Port 0.7	TIM5: input capture B input
11	E1		P0.8/OCMPA6	I/O	T_T			2mA	X	X	Port 0.8	TIM6: output compare A output
12	E2		P0.9/OCMPB6	I/O	T_T			2mA	X	X	Port 0.9	TIM6: output compare B output
13	E3		P0.10/OCMPA7	I/O	T_T			2mA	X	X	Port 0.10	TIM7: output compare A output
14	E4		P0.11/OCMPB7	I/O	T_T			2mA	X	X	Port 0.11	TIM7: output compare B output
15	F1	8	V _{DD}	S							Supply voltage (5 V)	
16	G1	9	V _{SS}	S							Ground	
17	E5	10	P0.12/ICAPA3	I/O	T_T			2mA	X	X	Port 0.12	TIM3: input capture A input
18	F2	11	P0.13/ICAPB3	I/O	T_T			2mA	X	X	Port 0.13	TIM3: input capture B input

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP		
119	B8	84	P5.9/PWM5	I/O	T _T		INT7	2mA	X	X	Port 5.9	PWM5: PWM output (TQFP100 only)
120	C8	85	P5.10/RDI2	I/O	T _T		INT8	2mA	X	X	Port 5.10	UART2: receive data input
121	A12	86	P5.11/TDO2	I/O	T _T		INT9	2mA	X	X	Port 5.11	UART2: transmit data output
122	D8	87	P5.12	I/O	T _T		INT10	2mA	X	X	Port 5.12	
123	E8		P5.13	I/O	T _T		INT11	2mA	X	X	Port 5.13	
124	B7		P5.14	I/O	T _T		INT12	2mA	X	X	Port 5.14	
125	A7		P5.15	I/O	T _T		INT13	2mA	X	X	Port 5.15	
126	A6	88	V ₁₈	S								1.8 V decoupling pin: a decoupling capacitor (recommended value: 100 nF) must be connected between this pin and nearest V _{SS} pin.
127	C7	89	V _{SS}	S								Ground
128	D7	90	V _{DD}	S								Supply voltage (5 V)
129	E7	91	P6.0	I/O	T _T		WUP0	8mA	X	X	Port 6.0	
130	F7		P6.1	I/O	T _T		WUP1	2mA	X	X	Port 6.1	
131	B6	92	P6.2/RDI3	I/O	T _T		WUP2	2mA	X	X	Port 6.2	UART3: receive data input
132	C6		P6.3	I/O	T _T		WUP3	2mA	X	X	Port 6.3	
133	D6	93	P6.4/TDO3	I/O	T _T		WUP4	2mA	X	X	Port 6.4	UART3: transmit data output
134	E6		P6.5	I/O	T _T		WUP5	2mA	X	X	Port 6.5	
135	A5	94	P6.6	I/O	T _T		WUP6	2mA	X	X	Port 6.6	
136	B5		P6.7	I/O	T _T		WUP7	2mA	X	X	Port 6.7	
137	C5	95	P6.8/RDI0	I/O	T _T		WUP10	2mA	X	X	Port 6.8	UART0: receive data input
138	A3	96	P6.9/TDO0	I/O	T _T			2mA	X	X	Port 6.9	UART0: transmit data output
139	A2		P6.10	I/O	T _T		WUP8	2mA	X	X	Port 6.10	
140	D5	97	P6.11/MISO0	I/O	T _T			2mA	X	X	Port 6.11	BSPI0: master input/slave output
141	A4	98	P6.12/MOSI0	I/O	T _T			2mA	X	X	Port 6.12	BSPI0: master output/slave input
142	B4	99	P6.13/SCK0	I/O	T _T		WUP11	2mA	X	X	Port 6.13	BSPI0: serial clock
143	C4	100	P6.14/ \overline{SS} 0	I/O	T _T			2mA	X	X	Port 6.14	BSPI0: slave select
144	B3		P6.15	I/O	T _T		WUP9	2mA	X	X	Port 6.15	

4.3 Operating conditions

Subject to general operating conditions for V_{DD} , and T_A .

Table 8. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCLK}	Internal CPU and system clock frequency	Accessing SRAM or Flash (zero wait state Flash access up to 36 MHz)	0	36	MHz
V_{DD}	Standard Operating Voltage		4.5	5.5	V
V_{DDA}	Operating analog reference voltage with respect to ground		4.5	$V_{DD}+0.1$	V
T_A	Ambient temperature range	6 partnumber suffix 7 partnumber suffix	-40 -40	85 105	°C

Table 9. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{VDD}	V_{DD} rise time rate	Subject to general operating conditions for T_A .	-	20	-	ms/V

Figure 8. STOP I_{DD} vs. V_{DD}

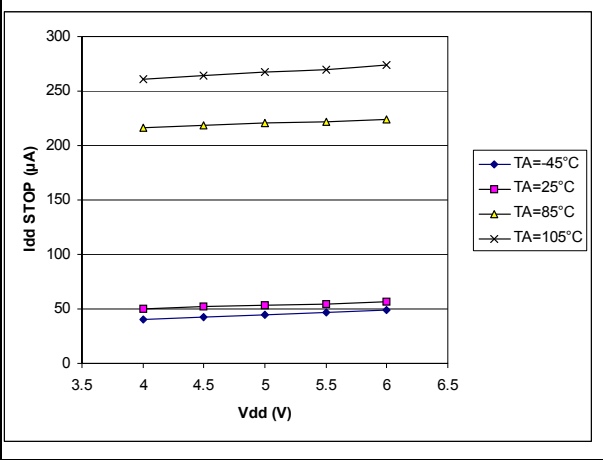


Figure 9. HALT I_{DD} vs. V_{DD}

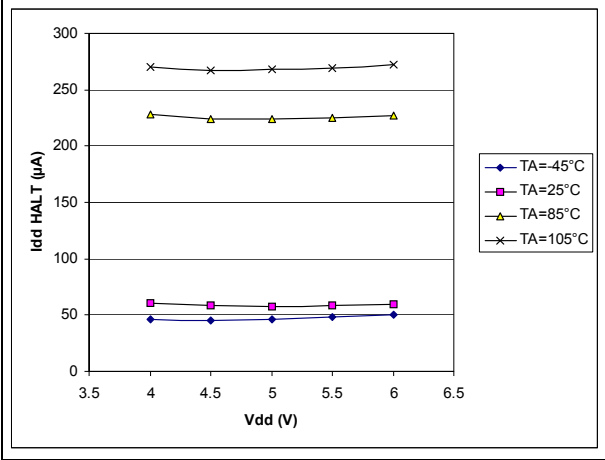


Figure 10. WFI I_{DD} vs. V_{DD}

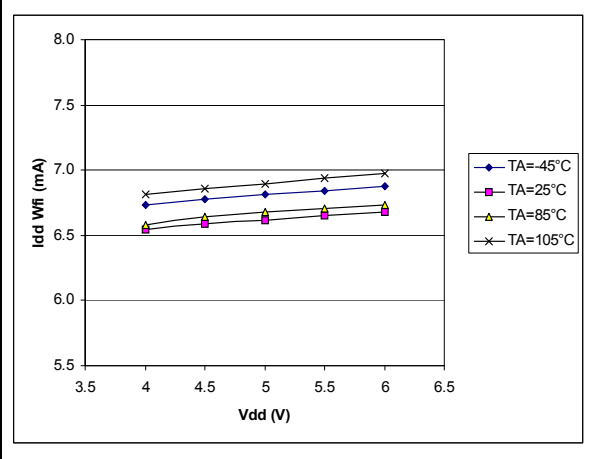
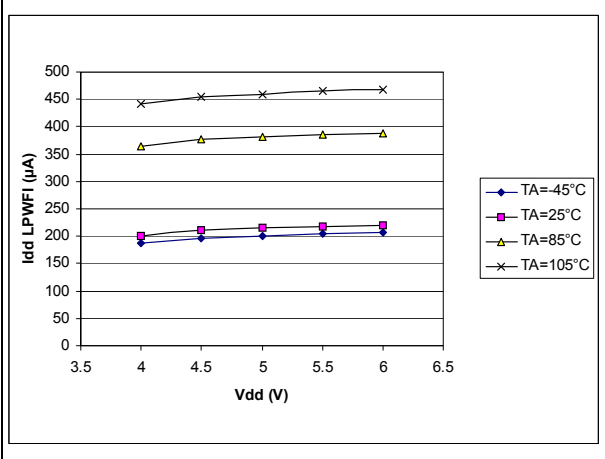


Figure 11. LPWFI I_{DD} vs. V_{DD}



Main oscillator characteristics

$V_{DD} = 5\text{ V} \pm 10\%$, $T_A = -40^\circ\text{C}$ to T_{Amax} , unless otherwise specified.

Table 14. Main oscillator characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
f_{OSC}	Oscillator frequency		4		8	MHz
g_m	Oscillator transconductance		1.5		4.2	mA/V
$V_{OSC}^{1)}$	Oscillation amplitude	$f_{OSC} = 4\text{ MHz}$, $T_A = 25^\circ\text{C}$	-	2.4	-	V
		$f_{OSC} = 8\text{ MHz}$, $T_A = 25^\circ\text{C}$		1.-		
$V_{AV}^{1)}$	Oscillator operating point	Sine wave middle, $T_A = 25^\circ\text{C}$	-	0.77	-	v
$t_{STUP}^{1)}$	Oscillator start-up time	External crystal, $V_{DD} = 5.5\text{ V}$, $f_{OSC} = 4\text{ MHz}$, $T_A = -40^\circ\text{C}$	-	-	12	ms
		External crystal, $V_{DD} = 5.0\text{ V}$, $f_{OSC} = 4\text{ MHz}$, $T_A = 25^\circ\text{C}$	-	5.5	-	ms
		External crystal, $V_{DD} = 5.5\text{ V}$, $f_{OSC} = 6\text{ MHz}$, $T_A = -40^\circ\text{C}$	-	-	8	ms
		External crystal, $V_{DD} = 5.0\text{ V}$, $f_{OSC} = 6\text{ MHz}$, $T_A = 25^\circ\text{C}$	-	3.3	-	ms
		External crystal, $V_{DD} = 5.5\text{ V}$, $f_{OSC} = 8\text{ MHz}$, $T_A = -40^\circ\text{C}$	-	-	7	ms
		External crystal, $V_{DD} = 5.0\text{ V}$, $f_{OSC} = 8\text{ MHz}$, $T_A = 25^\circ\text{C}$	-	2.7	-	ms

RC/backup oscillator characteristics

$V_{DD} = 5V \pm 10\%$, $T_A = -40^\circ\text{C}$ to T_{Amax} , unless otherwise specified.

Table 15. RC oscillator characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
f_{RC}	RC frequency	High frequency mode ¹⁾		2.35		MHz
		Low frequency mode ¹⁾		29		kHz
f_{RCHF}	RC high frequency	CMU_RCCTL = 0x0	3			MHz
		CMU_RCCTL = 0xF			2.3	MHz
f_{RCLF}	RC low frequency	CMU_RCCTL = 0x0	35			kHz
		CMU_RCCTL = 0xF			30	kHz
$f_{RCHFS}^{2)}$	RC high frequency stability	Fixed CMU_RCCTL			10	%
$f_{RCLFS}^{2)}$	RC low frequency stability	Fixed CMU_RCCTL			23	%
t_{RCSTUP}	RC start-up time	Stable V_{DD} , $f_{RC} = 2.35 \text{ MHz}$, $T_A = 25^\circ\text{C}$		2.35		μs

1) CMU_RCCTL = 0x8

2) RC frequency shift versus average value (%)

4.3.4 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electromagnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **ESD:** Electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- **FTB:** A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations:

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials:

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the RESET pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 19. EMS data

Symbol	Parameter	Conditions	Level/Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD}=5\text{ V}$, $T_A=+25^\circ\text{ C}$, $f_{MCLK}=36\text{ MHz}$ conforms to IEC 1000-4-2	4A
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	$V_{DD}=5\text{ V}$, $T_A=+25^\circ\text{ C}$, $f_{MCLK}=36\text{ MHz}$ conforms to IEC 1000-4-4	4A

4.3.5 I/O port pin characteristics

General characteristics

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 23. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage ¹⁾	TTL ports			0.8	V
V_{IH}	Input high level voltage ¹⁾		2.0			
$I_{INJ(PIN)}$	Injected current on any I/O pin				± 10	mA
$\Sigma I_{INJ(PIN)}$ ²⁾	Total injected current (sum of all I/O and control pins)				± 75	mA
I_{lkg}	Input leakage current ³⁾	$V_{SS} \leq V_{IN} \leq V_{DD}$			± 1	μA
I_S	Static current consumption ⁴⁾	Floating input mode		200		μA
R_{PU}	Weak pull-up equivalent resistor ⁵⁾	$V_{IN} = V_{SS}$	55	120	220	$k\Omega$
R_{PD}	Weak pull-down equivalent resistor ⁵⁾	$V_{IN} = V_{DD}$	55	120	220	$k\Omega$
C_{IO}	I/O pin capacitance			5		pF

1. Data based on characterization results, not tested in production.
2. When the current limitation is not possible, the V_{IN} absolute maximum rating must be respected, otherwise refer to $I_{INJ(PIN)}$ specification. A positive injection is induced by $V_{IN} > V_{33}$ while a negative injection is induced by $V_{IN} < V_{SS}$. Refer to [Section 4.2 on page 22](#) for more details.
3. Leakage could be higher than max. if negative current is injected on adjacent pins.
4. Configuration not recommended, all unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor. Data based on design simulation and/or technology characteristics, not tested in production.
6. The R_{PU} pull-up and R_{PD} pull-down equivalent resistor are based on a resistive transistor (corresponding I_{PU} and I_{PD} current characteristics described in [Figure 19](#)).

Output driving current

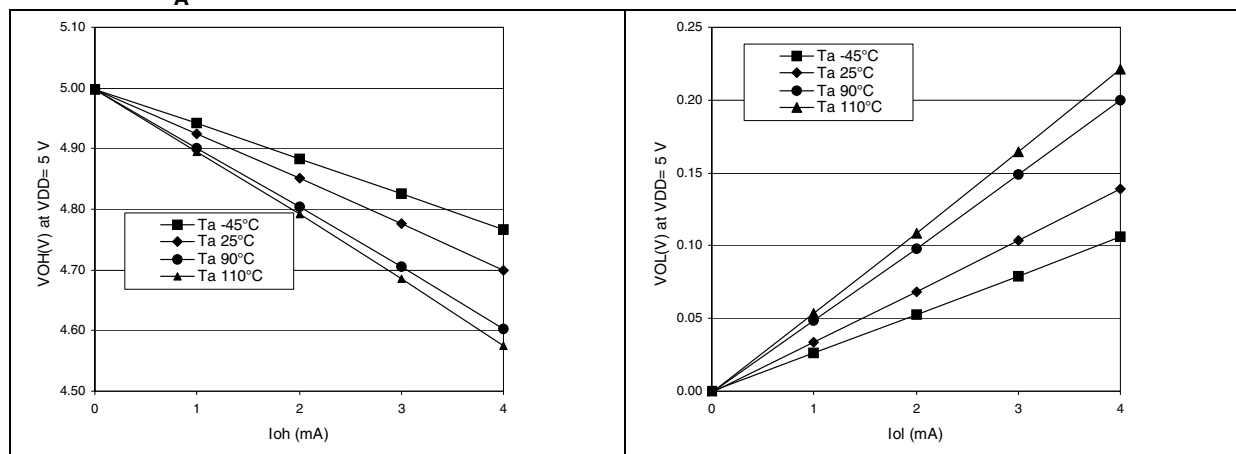
Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 24. Output driving current

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
Standard	$V_{OL}^{1)}$	Output low level voltage for an I/O pin when 8 pins are sunk at same time	$I_{IO}=+2$ mA		0.4	V
	$V_{OH}^{2)}$	Output high level voltage for an I/O pin when 4 pins are sourced at same time	$I_{IO}=-2$ mA	$V_{DD}-0.8$		
Med. Current (JTDO)	$V_{OL}^{1)}$	Output low level voltage for an I/O pin	$I_{IO}=+6$ mA		0.4	
	$V_{OH}^{2)}$	Output high level voltage for an I/O pin	$I_{IO}=-6$ mA	$V_{DD}-0.8$		
High Current P6.0	$V_{OL}^{1)}$	Output low level voltage for an I/O pin	$I_{IO}=+8$ mA		0.4	
	$V_{OH}^{2)}$	Output high level voltage for an I/O pin	$I_{IO}=-8$ mA	$V_{DD}-0.8$		

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in [Table 6](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS} .
2. The I_{IO} current sourced must always respect the absolute maximum rating specified in [Table 6](#) and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VDD} .

Figure 13. V_{OH} standard ports vs I_{OH} @ V_{DD} 5V **Figure 14. V_{OL} standard ports vs I_{OL} @ V_{DD} 5V**
 $T_A -45^\circ\text{C}$



4.3.6 10-bit ADC characteristics

Subject to general operating conditions for V_{DDA} , f_{MCLK} , and T_A unless otherwise specified.

Table 26. ADC characteristics

Symbol	Parameter	Conditions	Min	Typ ¹⁾	Max	Unit
f_{ADC}			0.4		10	MHz
V_{AIN}	Conversion voltage range ²⁾		V_{SSA}		V_{DDA}	V
I_{lkg}	Negative input leakage current on analog pins	$V_{IN} < V_{SS}$, $ I_{IN} < 400 \mu A$ on adjacent analog pin		5	6	μA
C_{ADC}	Internal sample and hold capacitor				3.5	pF
$t_{CAL}^{2)}$	Calibration time	$f_{ADC} = 10 \text{ MHz}$	580.2			μs
			5802			$1/f_{ADC}$
$t_S^{3)}$	Sampling time	$f_{ADC} = 10 \text{ MHz}$	1		14	μs
t_{CONV}	Total conversion time (including sampling time)	$f_{ADC} = 10 \text{ MHz}$	3			μs
			30 (10 for sampling +20 for successive approximation)			$1/f_{ADC}$
I_{ADC}	Running mode	Normal mode			5	mA
	Power-down mode				1	μA

1. Unless otherwise specified, typical data are based on $T_A=25^\circ C$ and $V_{DDA}-V_{SS}=5.0V$. They are given only as design guidelines and are not tested.
2. Calibration is recommended once after each power-up.
3. During the sample time the input capacitance C_{AIN} (6.8 max) can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_S . After the end of the sample time t_S , changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_S depend on programming.

Table 27. ADC accuracy with $f_{MCLK} = 20\text{ MHz}$, $f_{ADC} = 10\text{ MHz}$, $R_{AIN} < 10\text{ k}\Omega$, R_{AIN} , $V_{DDA} = 5\text{ V}$. This assumes that the ADC is calibrated²⁾

Symbol	Parameter	Conditions	Typ	Max	Unit
$ E_T $	Total unadjusted error ¹⁾		1.0	2.0	LSB
$ E_O $	Offset error ¹⁾		0.15	1.0	
$ E_G $	Gain error ¹⁾		0.97	1.1	
$ E_D $	Differential linearity error ¹⁾		0.7	1.0	
$ E_L $	Integral linearity error ¹⁾		0.76	1.5	

1. ADC accuracy vs. negative injection current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current. The effect of negative injection current on robust pins is specified in [Section 4.3.5](#). Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 4.3.5](#) does not affect the ADC accuracy.
2. Calibration is needed once after each power-up.

Figure 21. ADC accuracy characteristics

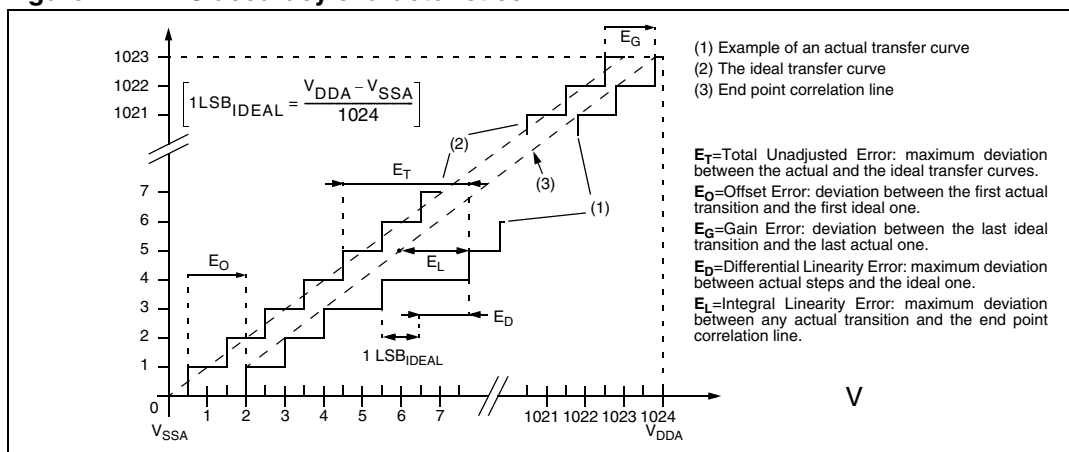
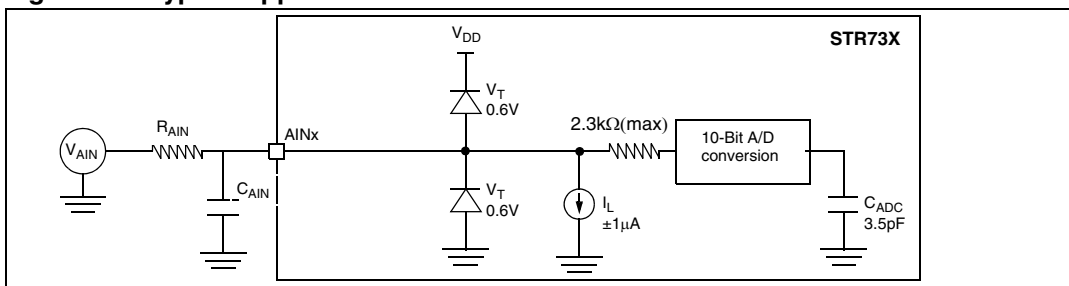


Figure 22. Typical application with ADC



Analog power supply and reference pins

The V_{DDA} and V_{SSA} pins are the analog power supply of the A/D converter cell. They act as the high and low reference voltages for the conversion.

Separation of the digital and analog power pins allow board designers to improve A/D performance. Conversion accuracy can be impacted by voltage drops and noise in the event of heavily loaded or badly decoupled power supply lines (see: [General PCB design guidelines](#)).

General PCB design guidelines

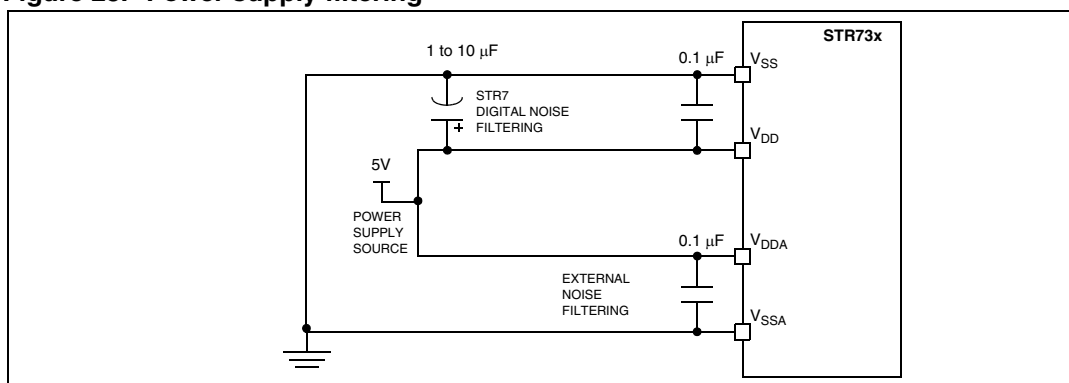
To obtain best results, some general design and layout rules should be followed when designing the application PCB to shield the noise-sensitive, analog physical interface from noise-generating CMOS logic signals.

- Use separate digital and analog planes. The analog ground plane should be connected to the digital ground plane via a single point on the PCB.
- Filter power to the analog power planes. It is recommended to connect capacitors, with good high frequency characteristics, between the power and ground lines, placing 0.1 μF and optionally, if needed 10 pF capacitors as close as possible to the STR7 power supply pins and a 1 to 10 μF capacitor close to the power source (see [Figure 23](#)).
- The analog and digital power supplies should be connected in a star network. Do not use a resistor, as V_{DDA} is used as a reference voltage by the A/D converter and any resistance would cause a voltage drop and a loss of accuracy.
- Properly place components and route the signal traces on the PCB to shield the analog inputs. Analog signals paths should run over the analog ground plane and be as short as possible. Isolate analog signals from digital signals that may switch while the analog inputs are being sampled by the A/D converter. Do not toggle digital outputs near the A/D input being converted.

Software filtering of spurious conversion results

For EMC performance reasons, it is recommended to filter A/D conversion outliers using software filtering techniques.

Figure 23. Power supply filtering



5.2 Thermal characteristics

The average chip-junction temperature, T_J , in degrees Celsius, may be calculated using the following equation:

$$T_J = T_A + (P_D \times \Theta_{JA}) \quad (1)$$

Where:

- T_A is the ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$),
- P_{INT} is the product of I_{DD} and V_{DD} , expressed in Watts. This is the chip internal power,
- $P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Most of the time for the applications $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant if the device is configured to drive continuously external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

$$P_D = K / (T_J + 273^\circ\text{C}) \quad (2)$$

Therefore (solving equations 1 and 2):

$$K = P_D \times (T_A + 273^\circ\text{C}) + \Theta_{JA} \times P_D^2 \quad (3)$$

Where:

- K is a constant for the particular part, which may be determined from equation (3) by measuring P_D (at equilibrium) for a known T_A . Using this value of K , the values of P_D and T_J may be obtained by solving equations (1) and (2) iteratively for any value of T_A

Table 28. Thermal characteristics

Symbol	Description	Package	Value (typical)	Unit
Θ_{JA}	Thermal resistance junction-ambient	LFBGA144	50	°C/W
		TQFP144	40	
		TQFP100	40	

6 Order codes

Table 29. Order codes

Partnumber	Flash Kbytes	Package	RAM Kbytes	TIM timers	6x PWM module	CAN periph	A/D chan.	Wake-up lines	I/O ports	Temp. range
STR730FZ1T6	128	TQFP144 20x20	16	10	1	3	16	32	112	-40 to +85°C
STR730FZ2T6	256									
STR730FZ1H6	128	LFBGA144 10x10								
STR730FZ2H6	256									
STR735FZ1T6	128	TQFP144 20x20				0				
STR735FZ2T6	256									
STR735FZ1H6	128	LFBGA144 10x10								
STR735FZ2H6	256									
STR731FV0T6	64	TQFP100 14x14		6		3	12	18	72	
STR731FV1T6	128									
STR731FV2T6	256									
STR736FV0T6	64	TQFP100 14x14								
STR736FV1T6	128									
STR736FV2T6	256									
STR730FZ1T7	128	TQFP144 20x20	16	10	1	3	16	32	112	-40 to +105°C
STR730FZ2T7	256									
STR730FZ1H7	128	LFBGA144 10x10								
STR730FZ2H7	256									
STR735FZ1T7	128	TQFP144 20x20				0				
STR735FZ2T7	256									
STR735FZ1H7	128	LFBGA144 10x10								
STR735FZ2H7	256									
STR731FV0T7	64	TQFP100 14x14		6		3	12	18	72	
STR731FV1T7	128									
STR731FV2T7	256									
STR736FV0T7	64	TQFP100 14x14								
STR736FV1T7	128									
STR736FV2T7	256									

7 Known limitations

7.1 Low power wait for interrupt mode

When the STR73x device is put in Low Power Wait For Interrupt mode (LPWFI), the Flash goes into low power mode or power down mode, depending on the setting of the PWD bit in the Flash Control Register 0 (default is '0', Low Power mode). This default mode can create excessive voltage conditions on the transistor gates and may affect the long term behavior of the Low Power mode circuitry.

Workaround

There is no workaround. If Low Power Wait For Interrupt mode is used, it is strongly suggested to configure the Flash to enter power down mode (bit PWD = '1').

7.2 PLL free running mode at high temperature

When the STR73x device is operated and an ambient temperature (T_A) of more than 55° C and the main system clock (f_{MCLK}) is sourced by the PLL in free running mode, the device may not work properly.

Workaround

At high temperature (more than 55° C), it is recommended to use the internal RC oscillator as a backup clock source rather than the PLL free running mode.